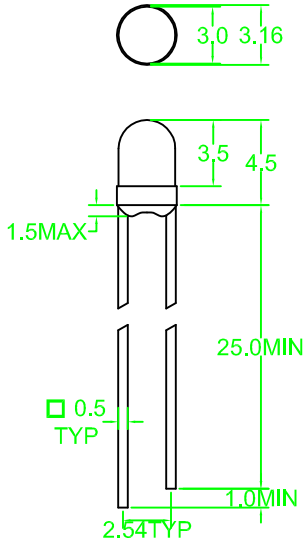


Package Dimension



Features

- High radiant intensity
- Suitable for pulsed applications
- Low average degradation

Description

The LVIR32643 series are high power solution grown epitaxial Gallium Arsenide infrared emitting diodes encapsulated in water clear plastic T-1 package individually

Note : 1.All dimension are in millimeter tolerance is $\pm 0.25\text{mm}$ unless otherwise noted.
2.Specifications are subject to change without notice

• Electrical Optical Characteristics (At 25°C)

PARAMETER	SYMBOL	PART NO	MIN	TYP	MAX	UNIT	TEST CONDITION
Radiant Intensity	Le	LVIR32643	3.0	5.0		mW/sr	IF=20mA
Aperture Radiant Incidence	Ee	LVIR32643	0.4	0.7		mW/cm ²	
Peak Emission Wavelength	λ peak			940		nm	IF=20mA
Spectral Line Half Width	$\Delta \lambda$			50		nm	IF=20mA
Forward Voltage	VF			1.2	1.6	V	IF=20mA
Reverse Current	IR			0	100	μ A	VR=5V
Viewing Angle	2 θ 1/2			36		deg	

• Absolute Maximum Rating (Ta=25°C)

PARAMETER	MAXIMUM	UNIT
Power Dissipation	100	mW
Peak Forward Current (300PPS, 1 μ s Pulse)	3	A
Continuous Forward Current	50	mA
Reverse Voltage	5	V
Operating Temperature Range	-55°C TO +100°C	
Storage Temperature Range	-55°C TO +100°C	
Lead Soldering Temperature 1.6mm(0.036") Form	260°C For 5 Seconds	